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[International Rectifier \(Infineon Technologies Americas Corp.\)
IRFU3708](#)

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SMPS MOSFET

PD - 93935B

IRFR3708

IRFU3708

HEXFET® Power MOSFET

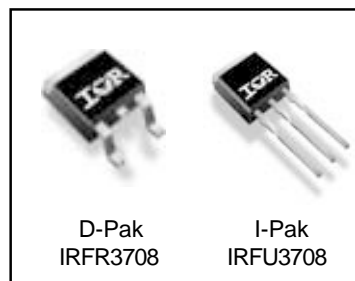
Applications

- High Frequency DC-DC Isolated Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Computer Processor Power

V_{DSS}	R_{DS(on)} max	I_D
30V	12.5mΩ	61A^④

Benefits

- Ultra-Low Gate Impedance
- Very Low R_{DS(on)} at 4.5V V_{GS}
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-to-Source Voltage	± 12	V
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	61 ④	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V	51 ④	
I _{DM}	Pulsed Drain Current①	244	
P _D @ T _A = 25°C	Maximum Power Dissipation③	87	W
P _D @ T _A = 70°C	Maximum Power Dissipation③	61	W
	Linear Derating Factor	0.58	W/°C
T _J , T _{STG}	Junction and Storage Temperature Range	-55 to + 175	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	1.73	°C/W
R _{θJA}	Junction-to-Ambient (PCB mount)*	—	50	
R _{θJA}	Junction-to-Ambient	—	110	

* When mounted on 1" square PCB (FR-4 or G-10 Material) .
For recommended footprint and soldering techniques refer to application note #AN-994

Notes ① through ④ are on page 9

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.028	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	8.5	12.5	m Ω	$V_{GS} = 10V, I_D = 15A$ ③
		—	10.0	14.0		$V_{GS} = 4.5V, I_D = 12A$ ③
		—	15.0	30.0		$V_{GS} = 2.8V, I_D = 7.5A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	0.6	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 12V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -12V$

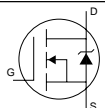
Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	49	—	—	S	$V_{DS} = 15V, I_D = 50A$
Q_g	Total Gate Charge	—	24	—	nC	$I_D = 24.8A$
Q_{gs}	Gate-to-Source Charge	—	6.7	—		$V_{DS} = 15V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	5.8	—		$V_{GS} = 4.5V$ ③
Q_{oss}	Output Gate Charge	—	14	21		$V_{GS} = 0V, I_D = 24.8A, V_{DS} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	7.2	—	ns	$V_{DD} = 15V$
t_r	Rise Time	—	50	—		$I_D = 24.8A$
$t_{d(off)}$	Turn-Off Delay Time	—	17.6	—		$R_G = 0.6\Omega$
t_f	Fall Time	—	3.7	—		$V_{GS} = 4.5V$ ③
C_{iss}	Input Capacitance	—	2417	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	707	—		$V_{DS} = 15V$
C_{riss}	Reverse Transfer Capacitance	—	52	—		$f = 1.0\text{MHz}$

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	213	mJ
I_{AR}	Avalanche Current①	—	62	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	61④	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	244		
V_{SD}	Diode Forward Voltage	—	0.88	1.3	V	$T_J = 25^\circ\text{C}, I_S = 31A, V_{GS} = 0V$ ③
		—	0.80	—		$T_J = 125^\circ\text{C}, I_S = 31A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	41	62	ns	$T_J = 25^\circ\text{C}, I_F = 31A, V_R = 20V$
Q_{rr}	Reverse Recovery Charge	—	64	96	nC	$di/dt = 100A/\mu s$ ③
t_{rr}	Reverse Recovery Time	—	43	65	ns	$T_J = 125^\circ\text{C}, I_F = 31A, V_R = 20V$
Q_{rr}	Reverse Recovery Charge	—	70	105	nC	$di/dt = 100A/\mu s$ ③

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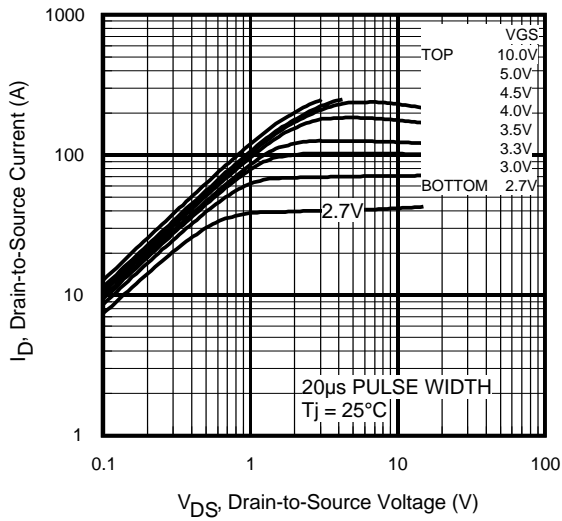


Fig 1. Typical Output Characteristics

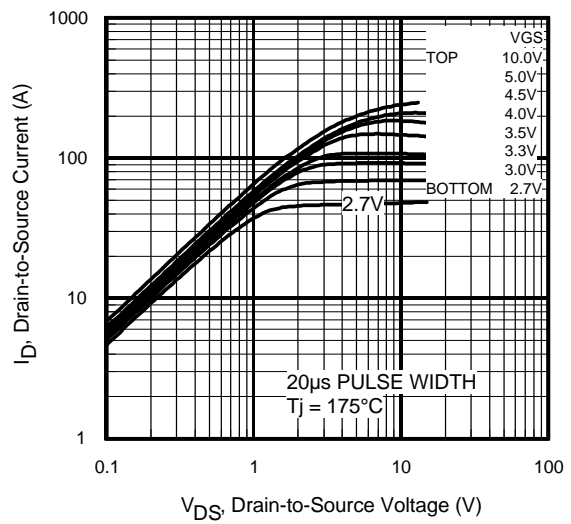


Fig 2. Typical Output Characteristics

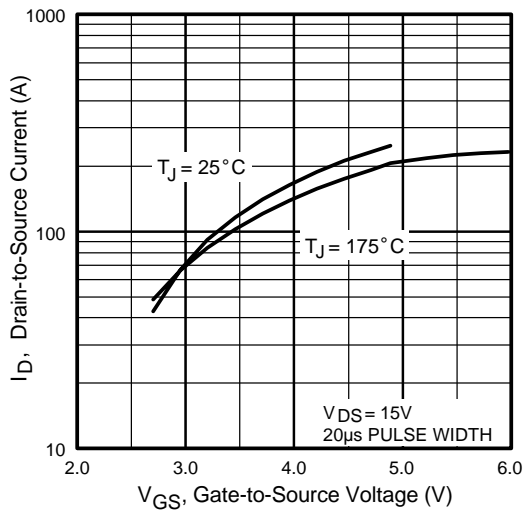


Fig 3. Typical Transfer Characteristics

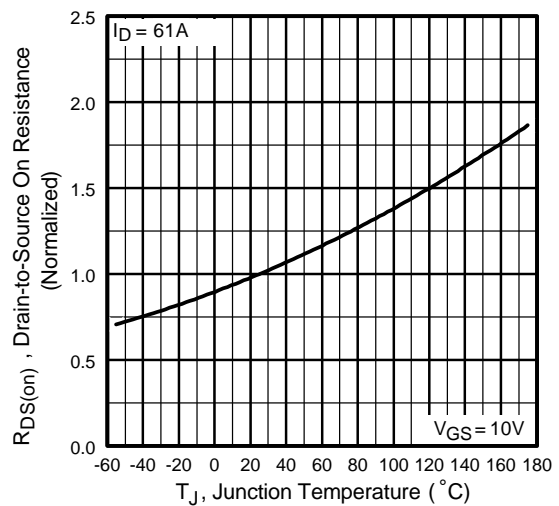


Fig 4. Normalized On-Resistance Vs. Temperature

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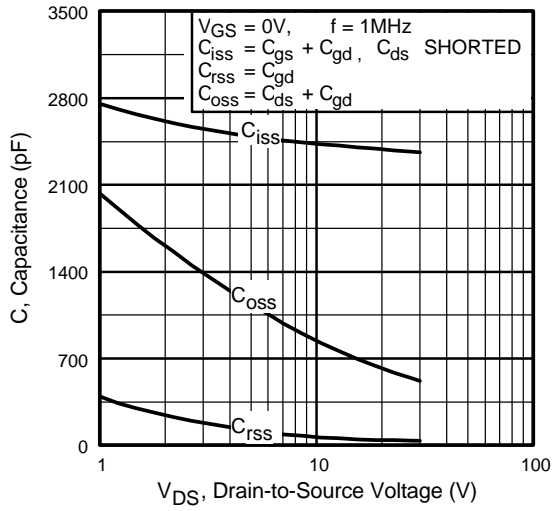


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

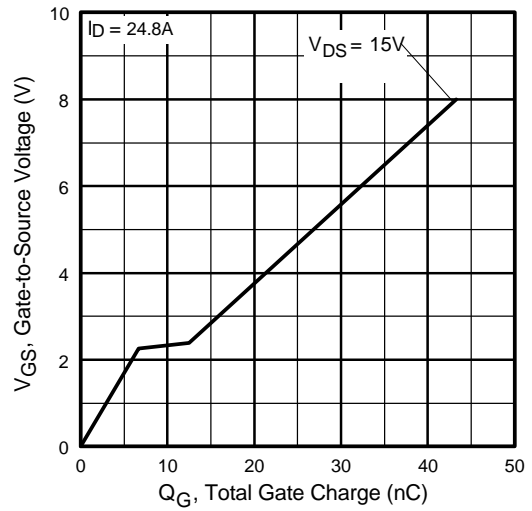


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

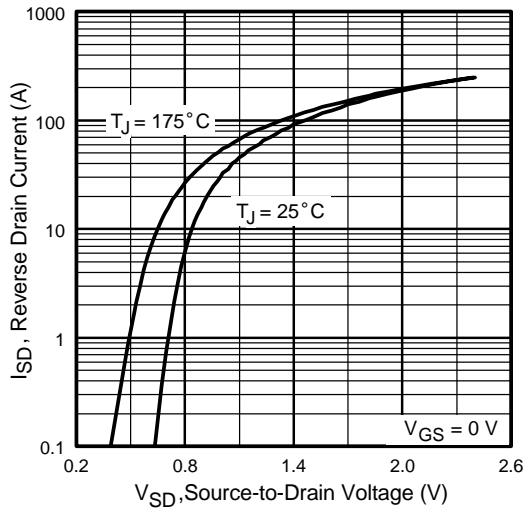


Fig 7. Typical Source-Drain Diode Forward Voltage

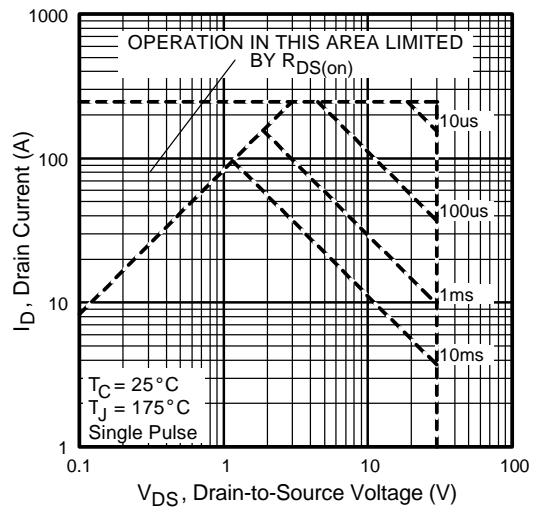


Fig 8. Maximum Safe Operating Area

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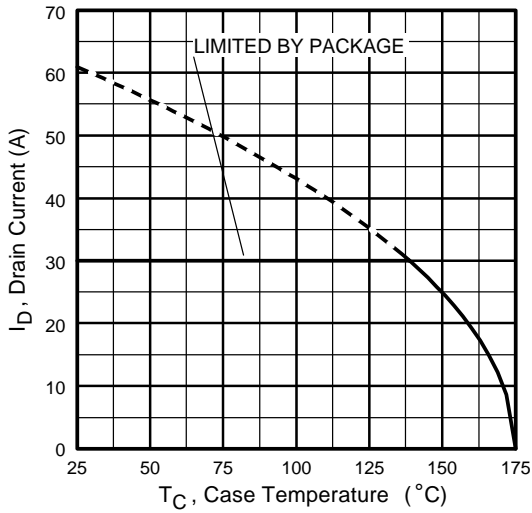


Fig 9. Maximum Drain Current Vs. Case Temperature

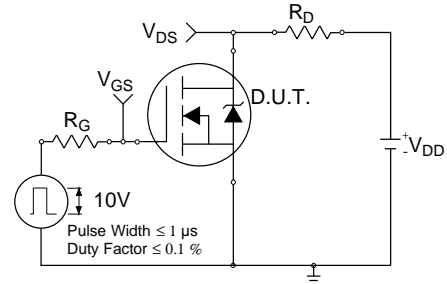


Fig 10a. Switching Time Test Circuit

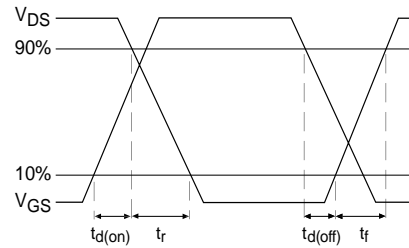


Fig 10b. Switching Time Waveforms

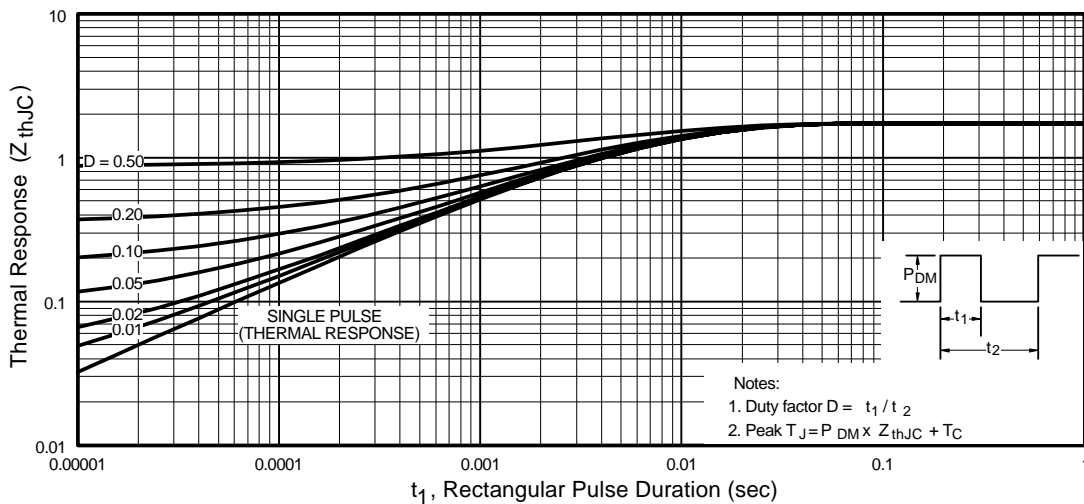


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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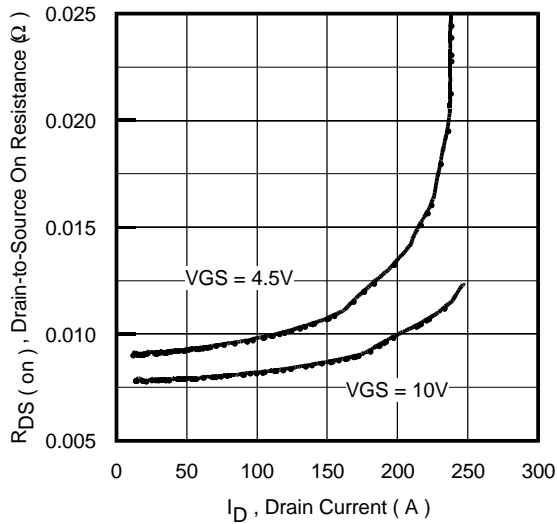


Fig 12. On-Resistance Vs. Drain Current

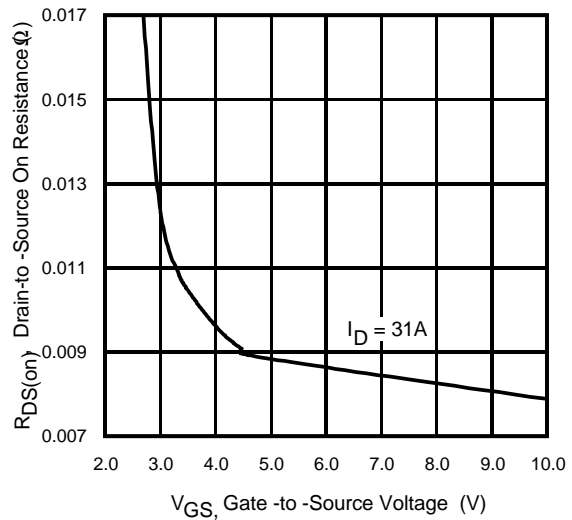


Fig 13. On-Resistance Vs. Gate Voltage

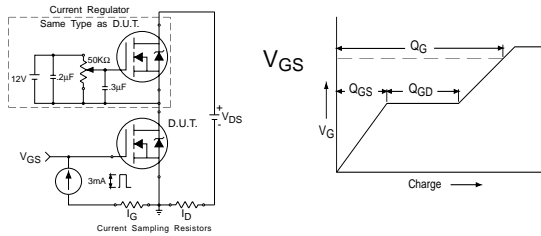


Fig 14a&b. Gate Charge Test Circuit and Waveform

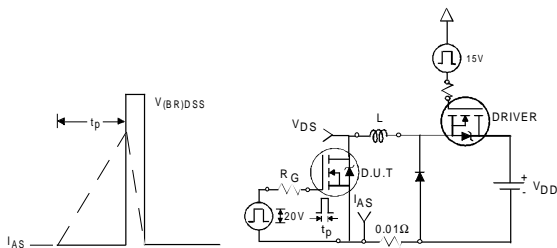


Fig 15a&b. Unclamped Inductive Test circuit and Waveforms

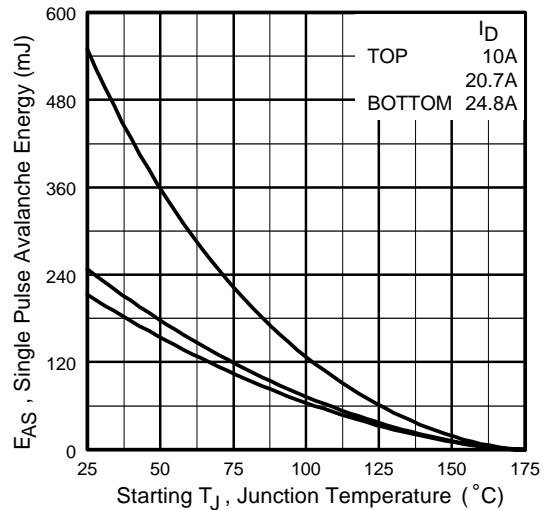


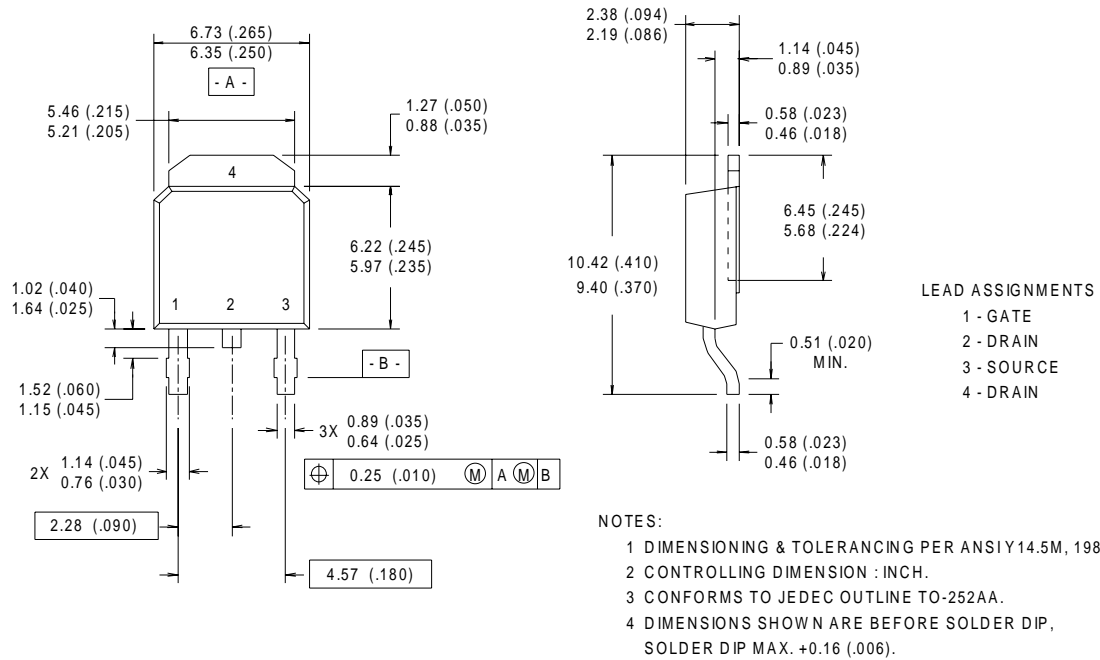
Fig 15c. Maximum Avalanche Energy Vs. Drain Current

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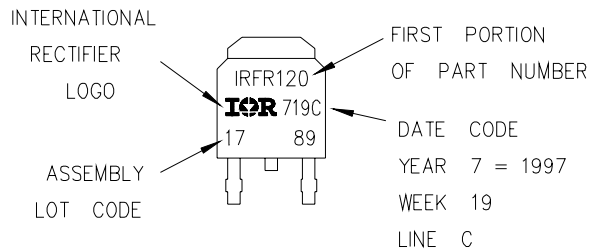
D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"

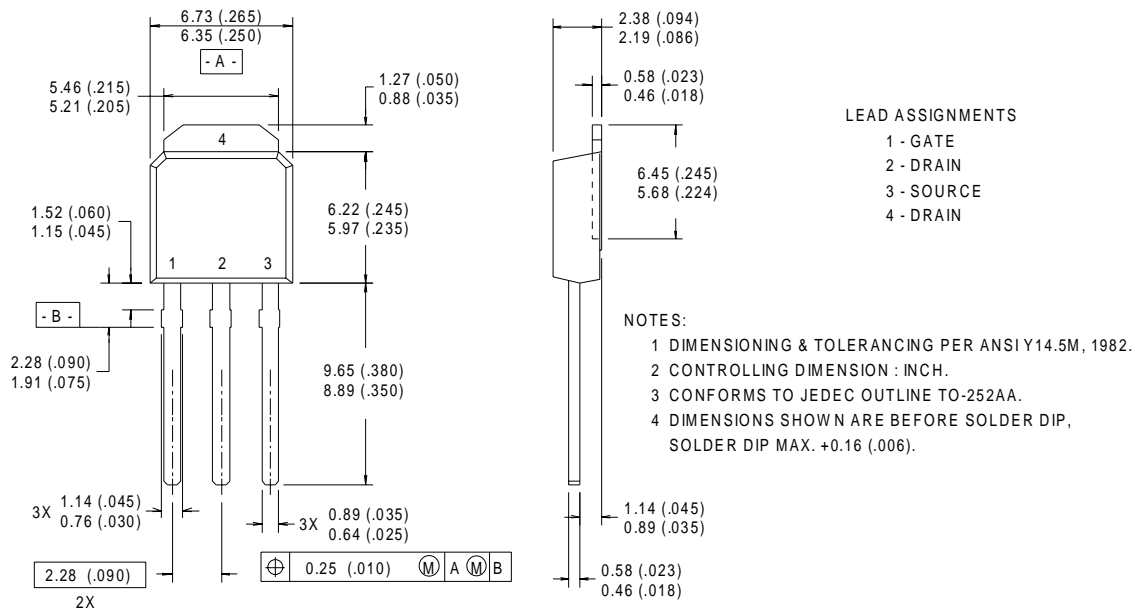


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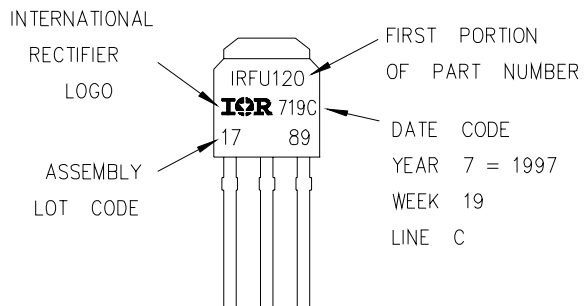
I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"

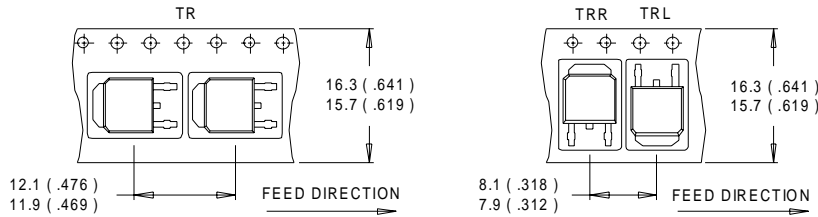


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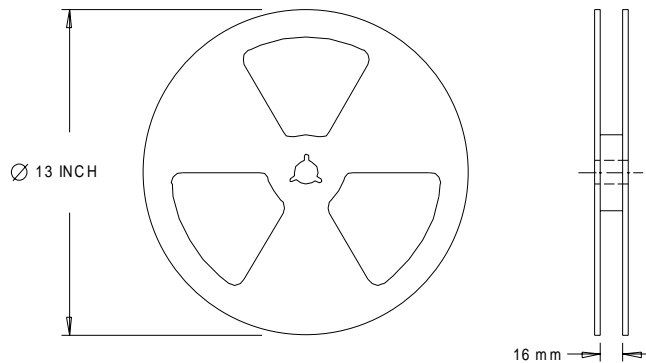
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D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.7 \text{ mH}$
 $R_G = 25\Omega$, $I_{AS} = 24.8 \text{ A}$.
- ③ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.

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IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
IR EUROPEAN REGIONAL CENTRE: 439/445 Godstone Rd, Whyteleafe, Surrey CR3 OBL, UK Tel: ++ 44 (0)20 8645 8000
IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200
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Data and specifications subject to change without notice. 8/00

Note: For the most current drawings please refer to the IR website at:
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